

9097250 TOSHIBA (DISCRETE/OPTO)

99D 16763 D T-39-13



SEMICONDUCTOR

TECHNICAL DATA

TOSHIBA FIELD EFFECT TRANSISTOR

2SK792

SILICON N CHANNEL MOS TYPE

(N-MOS)

HIGH SPEED, HIGH VOLTAGE SWITCHING APPLICATIONS.
SWITCHING REGULATOR AND MOTOR DRIVE APPLICATIONS.

FEATURES:

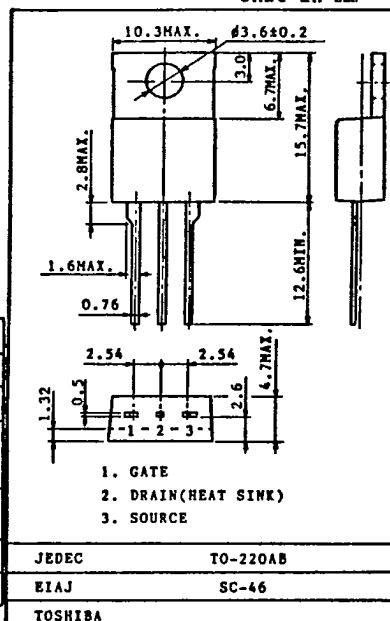
- High Breakdown Voltage : $V_{(BR)DSS}=900V$
- High Forward Transfer Admittance : $|Y_{fs}|=1.0S(Typ.)$
- Low Leakage Current : $I_{GSS}=\pm 100nA(Max.)$ @ $V_{GS}=\pm 20V$
 $I_{DSS}=300\mu A(Max.)$ @ $V_{DS}=900V$
- Enhancement-Mode : $V_{th}=1.5 \sim 3.5V$ @ $I_D=1mA$

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	900	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	DC	I_D	A
	Pulse	I_{DP}	
Drain Power Dissipation ($T_c=25^\circ C$)	P_D	100	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$

INDUSTRIAL APPLICATIONS

Unit in mm

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0$	-	-	± 100	nA
Drain Cut-off Current	I_{DSS}	$V_{DS}=900V, V_{GS}=0$	-	-	300	μA
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=10mA, V_{GS}=0$	900	-	-	V
Gate Threshold Voltage	V_{th}	$V_{DS}=10V, I_D=1mA$	1.5	-	3.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=1.5A$	0.5	1.0	-	S
Drain-Source ON Resistance	$R_{DS(ON)}$	$I_D=1.5A, V_{GS}=10V$	-	3.3	4.5	Ω
Drain-Source ON Voltage	$V_{DS(ON)}$	$I_D=3A, V_{GS}=10V$	-	12	15	V
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0, f=1MHz$	-	800	1100	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=25V, V_{GS}=0, f=1MHz$	-	70	120	pF
Output Capacitance	C_{oss}	$V_{DS}=25V, V_{GS}=0, f=1MHz$	-	120	200	pF
Switching Time	Rise Time		-	55	120	ns
	Turn-on Time		-	70	165	
	Fall Time		-	60	120	
	Turn-off Time		-	280	550	

TOSHIBA CORPORATION

GT1A2A

- 132 -

9097250 TOSHIBA (DISCRETE/OPTO)

99D 16764

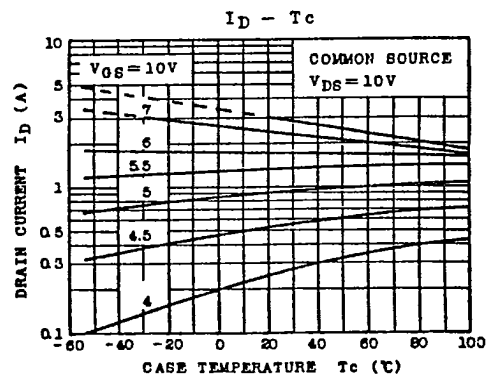
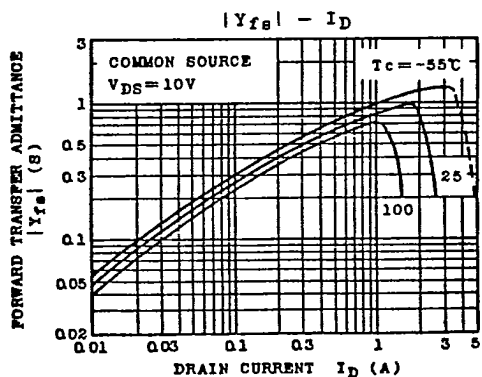
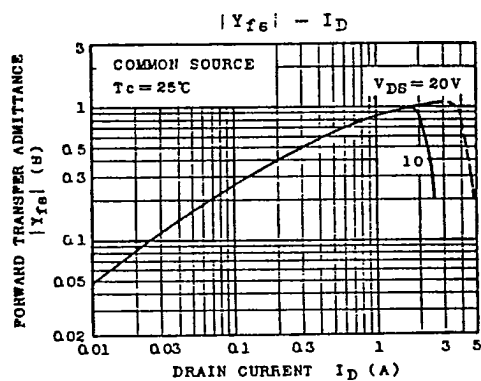
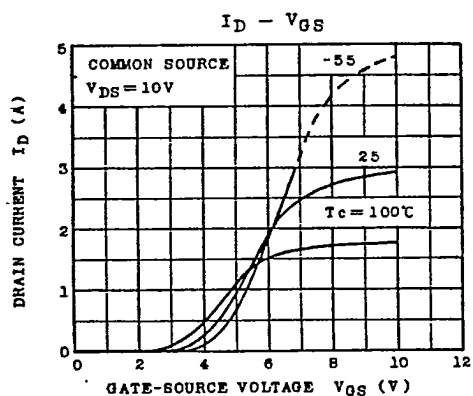
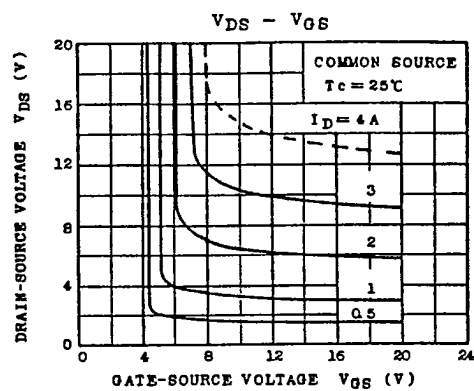
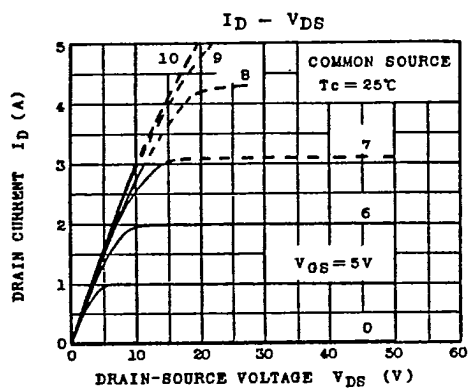
DT-39-13



SEMICONDUCTOR

TECHNICAL DATA

2SK792



TOSHIBA CORPORATION

GT1A2A

- 133 -

9097250 TOSHIBA (DISCRETE/OPTO)

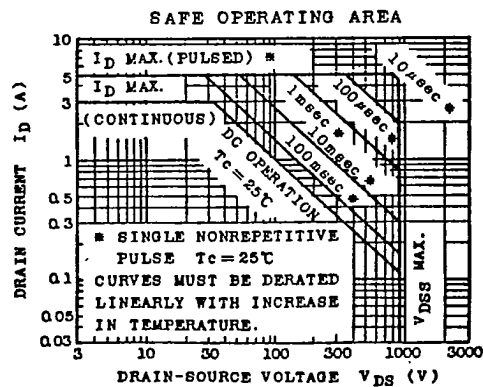
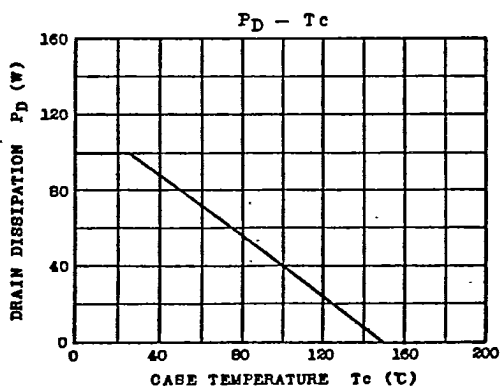
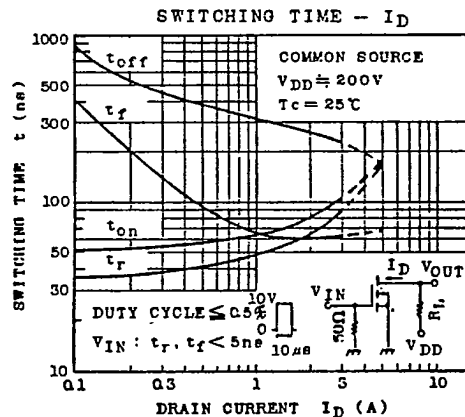
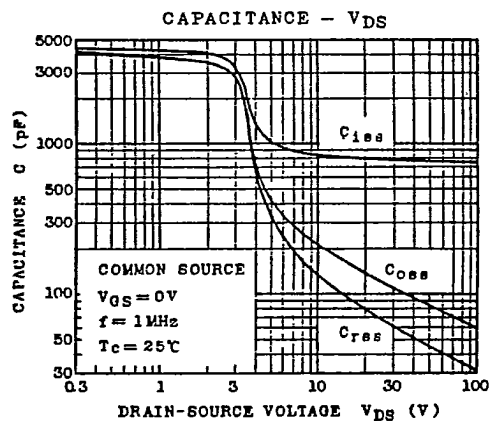
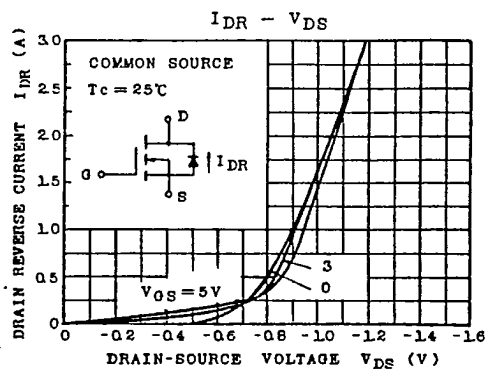
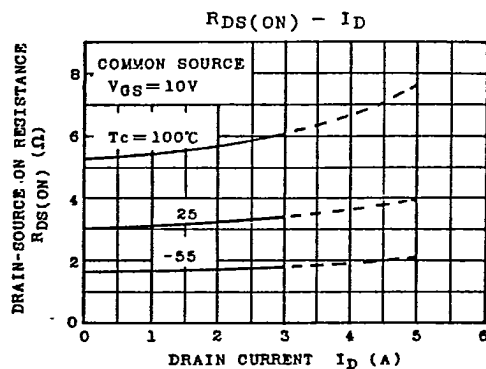
99D 16765 DT-39-13



SEMICONDUCTOR

TECHNICAL DATA

2SK792



TOSHIBA CORPORATION

GT1A2A

- 134 -